

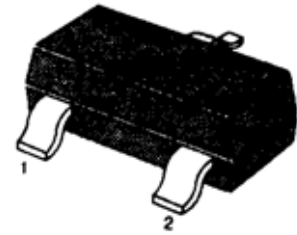
■■ APPLICATION: Interface Circuit and Driver Circuit Applications.

—NPN silicon—

■■ MAXIMUM RATINGS (Ta=25°C)

SOT-323

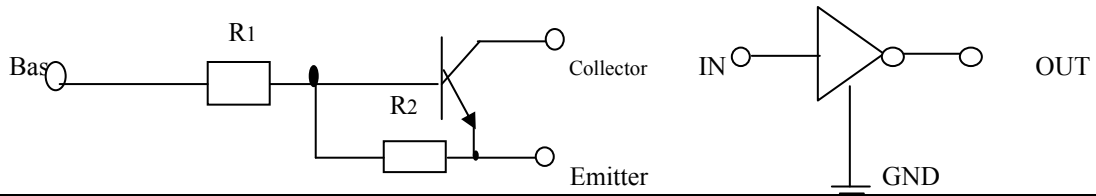
PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V <sub>CC</sub>	50	V
Input Voltage	V <sub>in</sub>	-10~+12	V
Output Current	I <sub>o</sub>	30	mA
	I <sub>C (max)</sub>	100	
Collector Power Dissipation	P <sub>C</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C



1. Base 2. Emitter 3. Collector

■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	68				V <sub>o</sub> = 5V, I <sub>o</sub> = 5 mA
Input Voltage	V <sub>i (off)</sub>			0.5	V	V <sub>CC</sub> = 5V, I <sub>o</sub> = 100μA
	V <sub>i (on)</sub>	3				V <sub>o</sub> = 0.3V, I <sub>o</sub> = 2 mA
Output Voltage	V <sub>o (on)</sub>			0.3	V	I <sub>o</sub> = 10mA, I <sub>i</sub> = 0.5mA
Input Current	I <sub>i</sub>			0.18	mA	V <sub>i</sub> =5V
Output Current	I <sub>o (off)</sub>			0.5	μA	V <sub>CC</sub> = 50V, V <sub>i</sub> = 0V
Input Resistance	R <sub>1</sub>	32.9	47	61.1	KΩ	
Output Resistance	R <sub>2</sub>	32.9	47	61.1	KΩ	
Gain bandwidth product	f <sub>T</sub>	150	250		MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA, f=100MHz



■■ h<sub>FE</sub> Classification And Marking

Print Mark	26
Classification	>68
h <sub>FE</sub>	